HM62832H Series

32768-word × 8-bit High Speed CMOS Static RAM

HITACHI

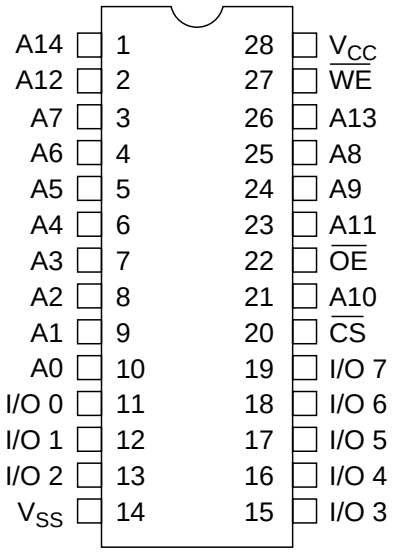
Features

- High speed: Fast access time 25/35/45 ns (max)
- Low power
  Active: 300 mW (typ)
  Standby: 10 µW (typ) (L-version)
- Single 5 V supply
- Completely static memory
  No clock or timing strobe required
- Equal access and cycle times
- Common data input and output – Three state output
- Directly TTL compatible – All inputs and outputs

Ordering Information

Type No.	Access Time	Package
HM62832HP-25	25 ns	300-mil 28-pin plastic DIP (DP-28NA)
HM62832HP-35	35 ns	
HM62832HP-45	45 ns	
HM62832HLP-25	25 ns	
HM62832HLP-35	35 ns	
HM62832HLP-45	45 ns	
HM62832HJP-25	25 ns	300-mil 28-pin plastic SOJ (CP-28DN)
HM62832HJP-35	35 ns	
HM62832HJP-45	45 ns	
HM62832HLJP-25	25 ns	
HM62832HLJP-35	35 ns	
HM62832HLJP-45	45 ns	

Pin Arrangement

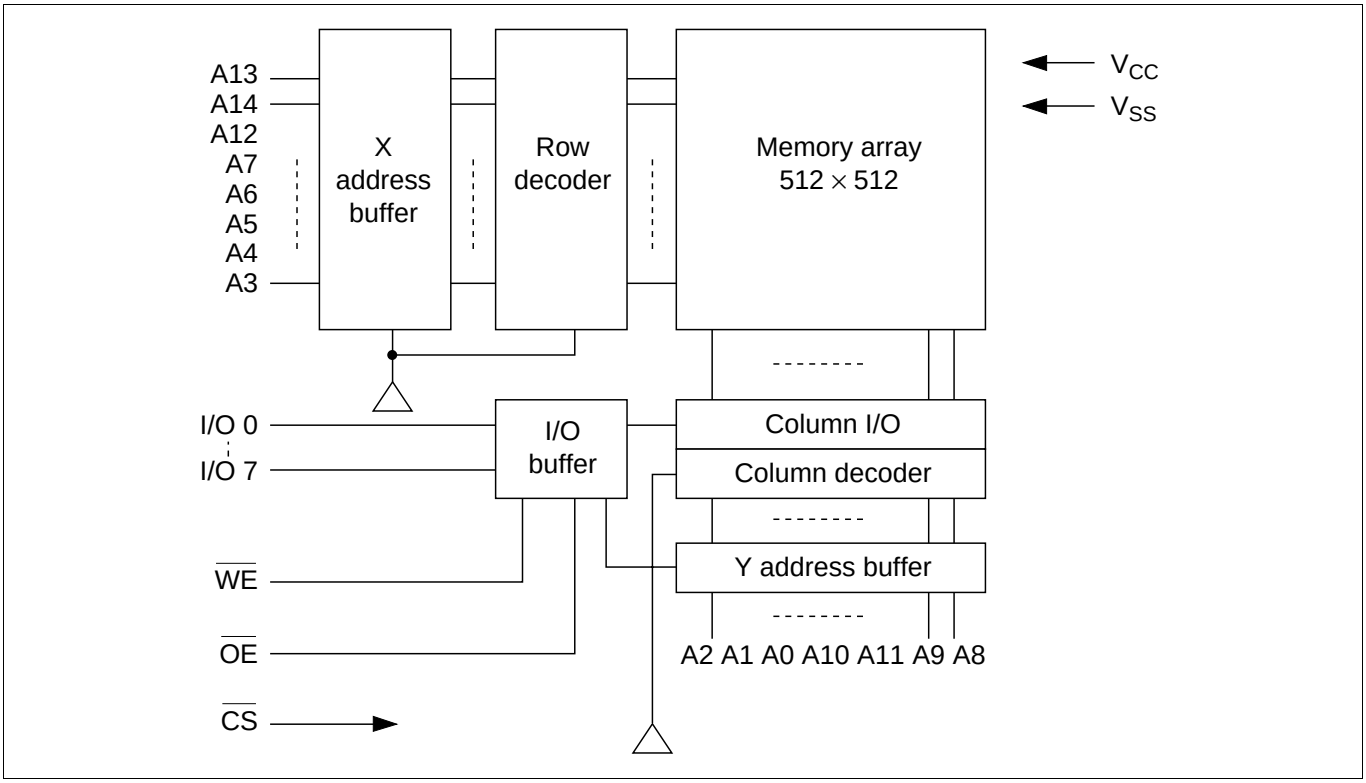


(Top view)

Pin Description

Pin Name	Function
A0 – A14	Address
I/O0 – I/O7	Input/output
$\overline{CS}$	Chip select
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
V_{CC}	Power supply
V_{SS}	Ground

Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	V_T	–0.5 [*1] to +7.0	V
Power dissipation	P_T	1.0	W
Operating temperature	Topr	0 to +70	°C
Storage temperature	Tstg	–55 to +125	°C
Storage temperature under bias	Tbias	–10 to +85	°C

Note: 1. –2.5 V for pulse width ≤ 10 ns

Function Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	Mode	V_{cc} Current	I/O Pin	Ref. Cycle
H	X	X	Not selected	I_{SB}, I_{SB1}	High-Z	
L	L	H	Read	I_{CC}	Dout	Read cycle (1) to (3)
L	H	L	Write	I_{CC}	Din	Write cycle (1)
L	L	L		I_{CC}	Din	Write cycle (2)

Note: X: H or L

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input voltage	V_{IH}	2.2	—	6.0	V
	V_{IL}	–0.5 *1	—	0.8	V

Note: 1. –2.0 V for pulse width ≤ 10 ns

DC Characteristics (Ta = 0 to +70°C, V_{CC} = 5 V ± 10%, V_{SS} = 0 V)

Parameter	Symbol	Min	Typ*1	Max	Unit	Test Conditions	Note
Input leakage current	$\|I_{LI}\|$	—	—	2	µA	Vin = V_{SS} to V_{CC}	
Output leakage current	$\|I_{LO}\|$	—	—	2	µA	$\overline{CS}$ = V_{IH} or $\overline{OE}$ = V_{IH} or $\overline{WE}$ = V_{IL}, $V_{I/O}$ = V_{SS} to V_{CC}	
Operating power supply current	I_{CC}	—	60	120	mA	Min cycle, duty = 100%, $\overline{CS}$ = V_{IL}, $I_{I/O}$ = 0 mA	
Standby power supply current	I_{SB}	—	15	30	mA	$\overline{CS}$ = V_{IH}	
Standby power supply current	I_{SB1}	—	0.02	2	mA	$\overline{CS}$ ≥ V_{CC} – 0.2 V, 0 V ≤ Vin ≤ 0.2 V or Vin ≥ V_{CC} – 0.2 V	
		—	0.002	0.1	mA		L-version
Output voltage	V_{OL}	—	—	0.4	V	I_{OL} = 8 mA	
	V_{OH}	2.4	—	—	V	I_{OH} = –4 mA	

Note: 1. Typical values are at V_{CC} = 5.0 V, Ta = +25°C and not guaranteed.

Capacitance (Ta = 25°C, f = 1.0 MHz)*1

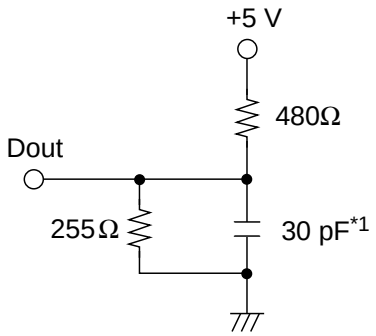
Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Input capacitance	Cin	—	—	6	pF	Vin = 0 V
Input/output capacitance	$C_{I/O}$	—	—	10	pF	$V_{I/O}$ = 0 V

Note: 1. This parameter is sampled and not 100% tested.

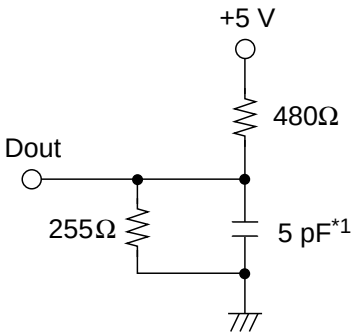
AC Characteristics (Ta = 0 to +70°C, V_{CC} = 5 V ± 10%, unless otherwise noted.)

Test Conditions

- Input pulse levels: 0.0 V to 3.0 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures



Output load (A)



Output load (B)
(for t_{CLZ}, t_{OLZ}, t_{CHZ}, t_{OHZ}, t_{WHZ} and t_{OW})

Note: 1. Including scope and jig

Read Cycle

		HM62832H-25		HM62832H-35		HM62832H-45			
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Unit**	**Note**
Read cycle time	t_{RC}	25	—	35	—	45	—	ns	
Address access time	t_{AA}	—	25	—	35	—	45	ns	
Chip select access time	t_{ACS}	—	25	—	35	—	45	ns	
Output enable to output valid	t_{OE}	—	12	—	15	—	20	ns	
Output hold from address change	t_{OH}	5	—	5	—	5	—	ns	6
Chip selection to output in low-Z	t_{CLZ}	5	—	5	—	5	—	ns	1
Output enable to output in low-Z	t_{OLZ}	0	—	0	—	0	—	ns	1
Chip deselection to output in high-Z	t_{CHZ}	0	12	0	15	0	20	ns	1
Output enable to output in high-Z	t_{OHZ}	0	12	0	15	0	20	ns	1

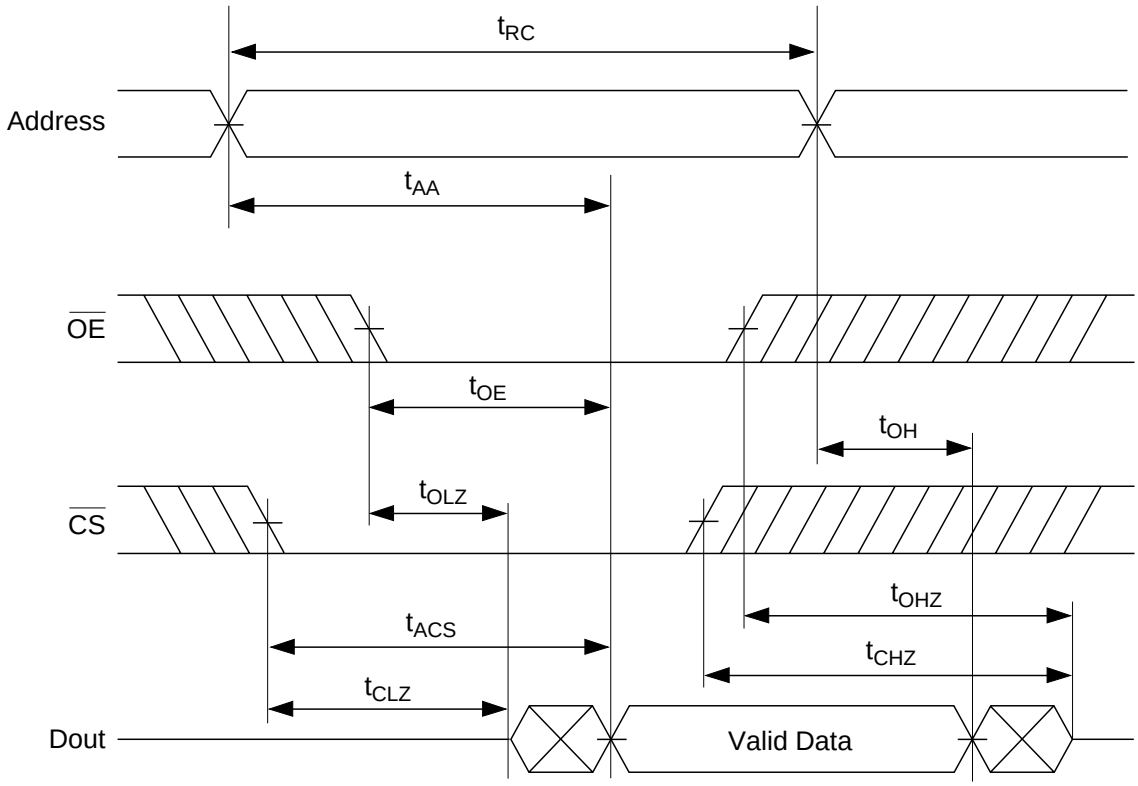
Write Cycle

Parameter	Symbol	HM62832H-25 Min	HM62832H-25 Max	HM62832H-35 Min	HM62832H-35 Max	HM62832H-45 Min	HM62832H-45 Max	Unit	Notes
Write cycle time	t_{WC}	25	—	35	—	45	—	ns	
Chip selection to end of write	t_{CW}	15	—	20	—	25	—	ns	
Address valid to end of write	t_{AW}	20	—	30	—	40	—	ns	
Address setup time	t_{AS}	0	—	0	—	0	—	ns	
Write pulse width	t_{WP}	15	—	20	—	25	—	ns	3
Write recovery time	t_{WR}	0	—	0	—	0	—	ns	4
Write to output in high-Z	t_{WHZ}	0	12	0	15	0	20	ns	2, 5
Data to write time overlap	t_{DW}	12	—	15	—	20	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	0	—	ns	
Output disable to output in high-Z	t_{OHZ}	0	12	0	15	0	20	ns	2, 5
Output active from end of write	t_{OW}	5	—	5	—	5	—	ns	2, 7

Notes:
1. Transition is measured ±200 mV from steady state voltage with load (B). This parameter is sampled and not 100% tested.
2. Transition is measured ±200 mV from high impedance voltage with load (B). This parameter is sampled and not 100% tested.
3. A write occurs during the overlap (t_{WP}) of a low $\overline{CS}$ and a low $\overline{WE}$.
4. t_{WR} is measured from the ealier of $\overline{CS}$ or $\overline{WE}$ going high to the end of write cycle.
5. During this period, I/O pins are in the output state. The input signals out of phase must not be applied.
6. Dout is in the same phase of written data of this write cycle.
7. If $\overline{CS}$ is low during this period, I/O pins are in the output state. The input signals out of phase must not be applied to I/O pins.

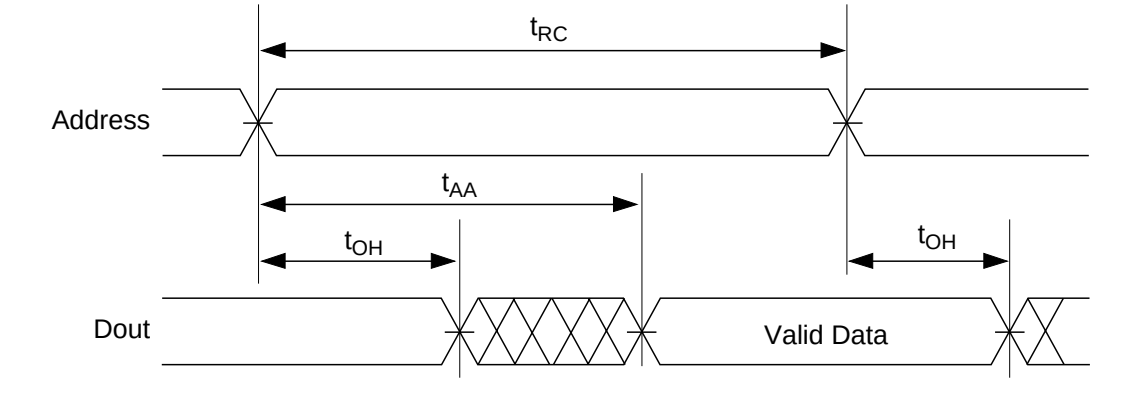
Timing Waveforms

Read Cycle Timing–1[*1] ($\overline{WE}$ = V_{IH})

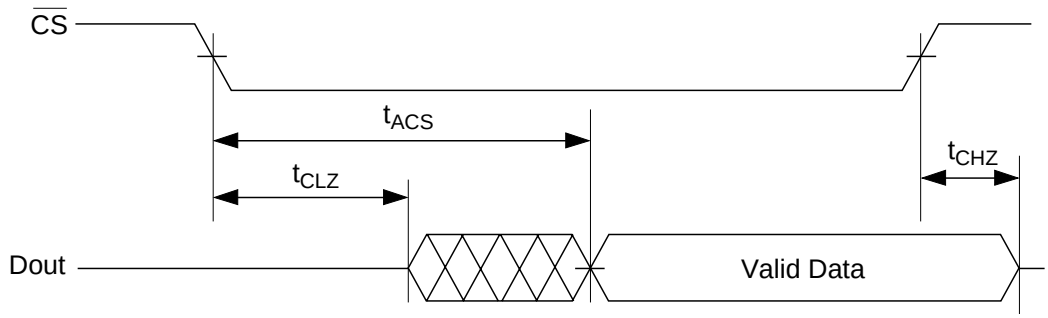


Note: 1. Transition is measured ±200 mV from steady state voltage with Load (B). This parameter is sampled and not 100% tested.

Read Cycle Timing–2 ($\overline{WE}$ = V_{IH}, $\overline{CS}$ = V_{IL}, $\overline{OE}$ = V_{IL})

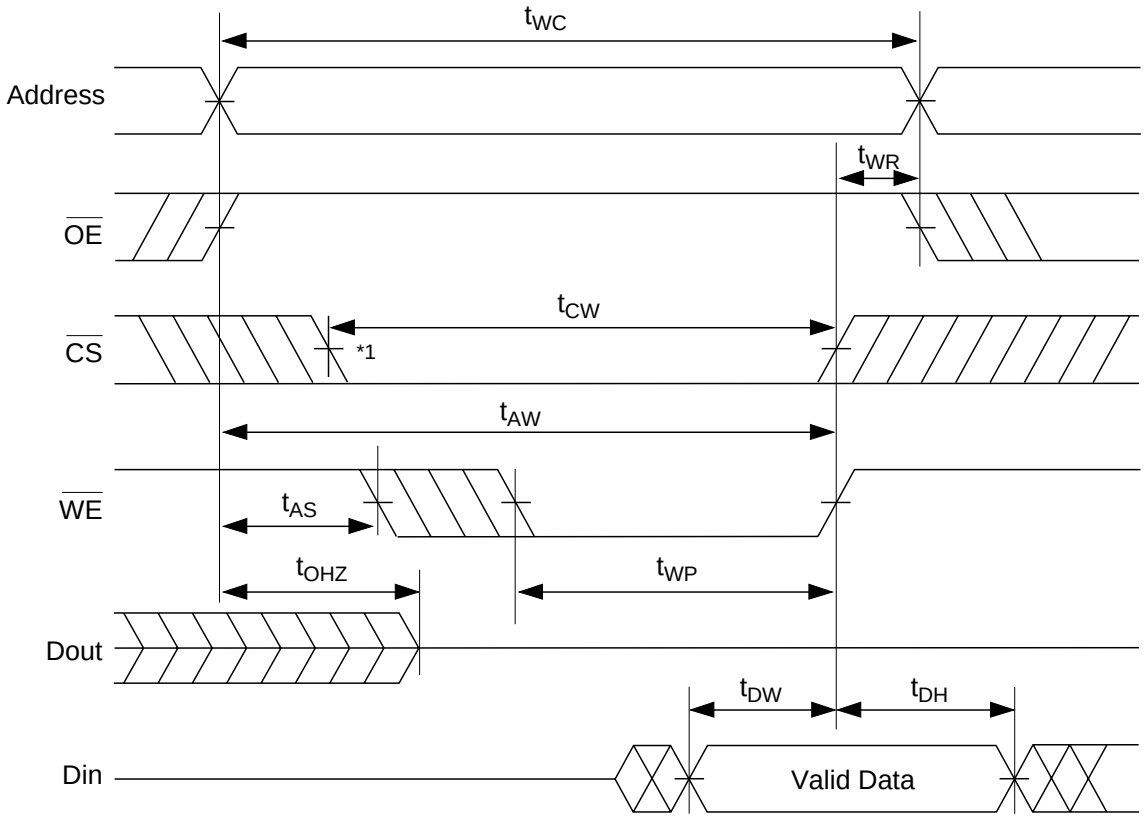


Read Cycle Timing–3[*1] ($\overline{WE}$ = V_{IH}, $\overline{OE}$ = V_{IL})



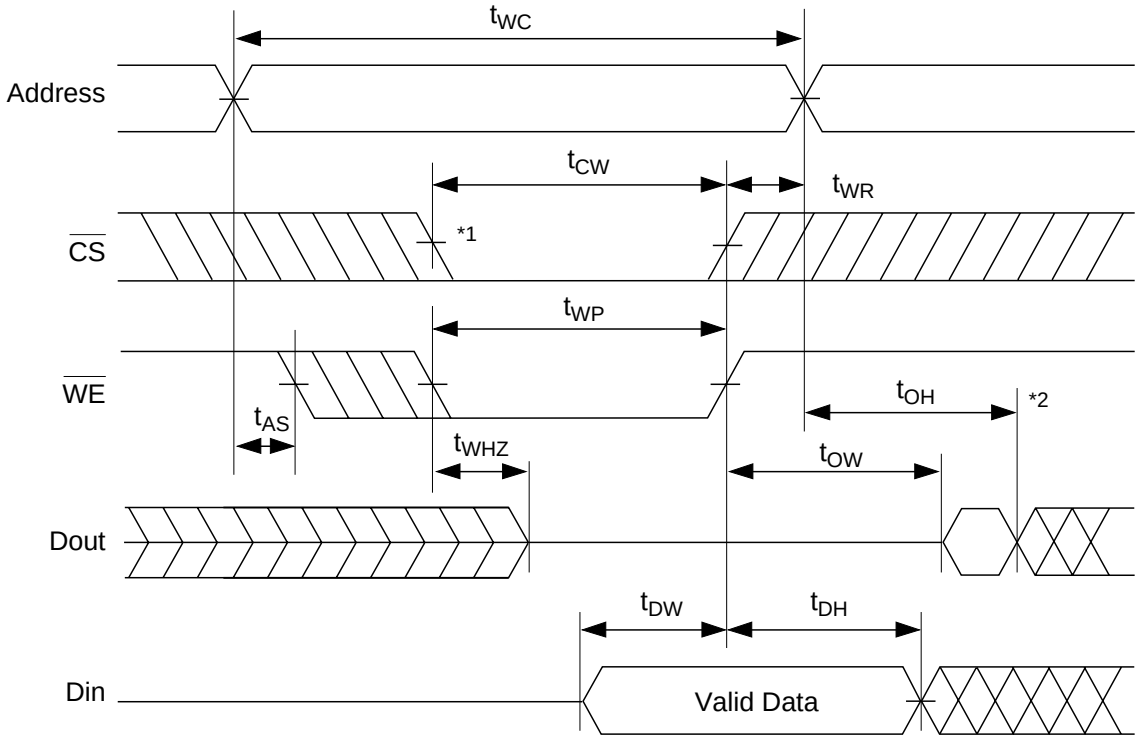
Notes: 1. Transition is measured ±200 mV from steady state voltage with load (B). This parameter is sampled and not 100% tested.
2. Address should be valid prior to or coincident with $\overline{CS}$ transition low.

Write Cycle Timing–1[*2]



Notes: 1. If the $\overline{CS}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ low transition, outputs remain in a high impedance state.
2. $\overline{WE}$ must be high during all address transitions except when device is deselected with $\overline{CS}$.

Write Cycle Timing–2[*3] (OE Low Fixed)



Notes: 1. If the CS low transition occurs simultaneously with the WE low transition or after the WE low transition, outputs remain in a high impedance state.

2. Dout is the read data of next address.

3. WE must be high during all address transitions except when device is deselected with CS.

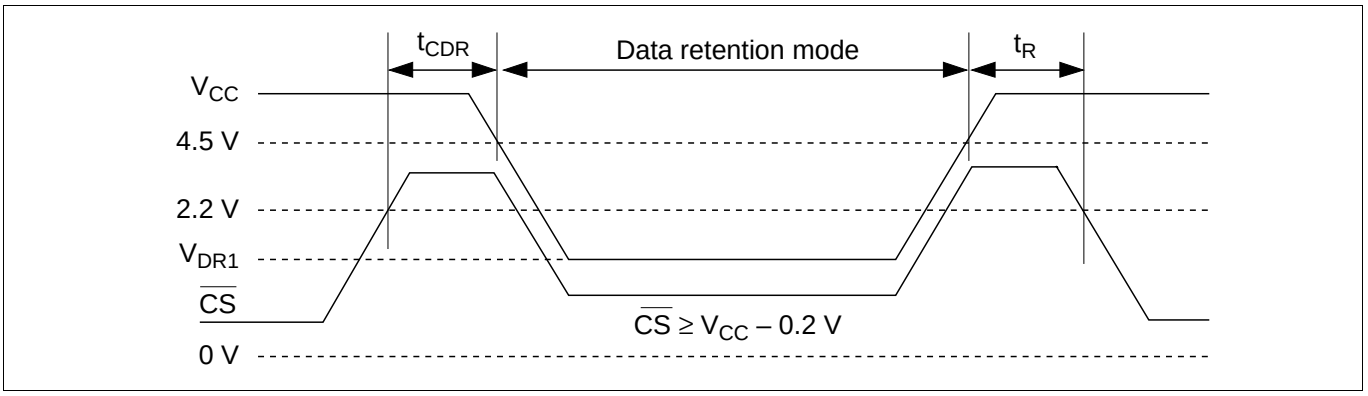
Low V_{CC} Data Retention Characteristics (Ta = 0 to +70°C)

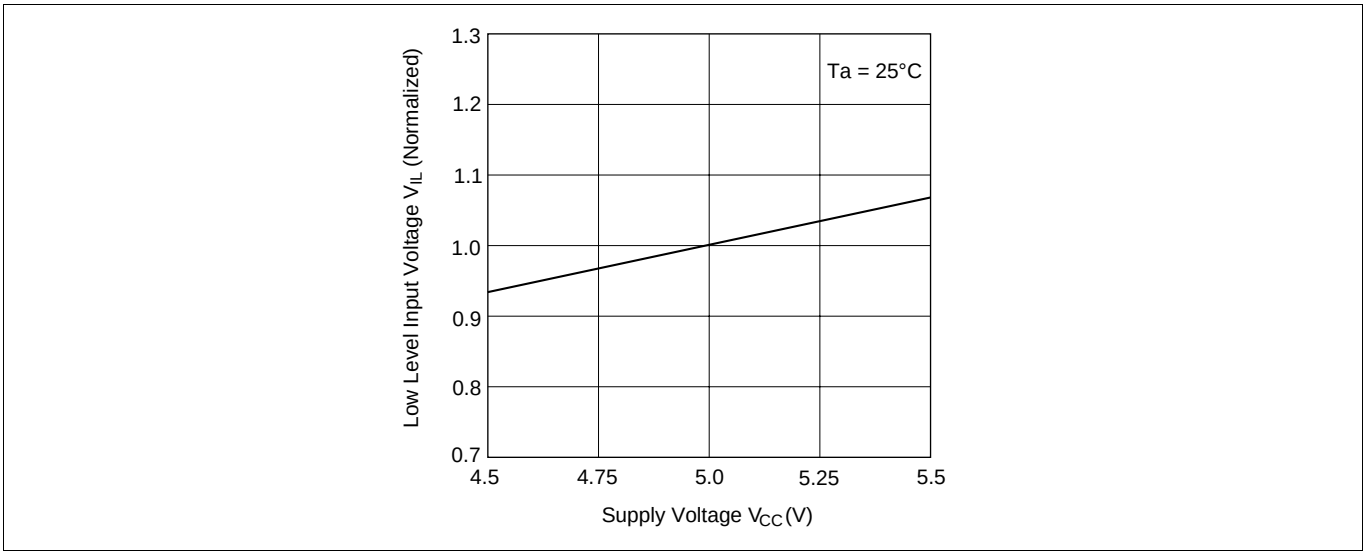
This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$\overline{CS} \geq V_{CC} - 0.2$ V, Vin $\geq V_{CC} - 0.2$ V or 0 V ≤ Vin ≤ 0.2 V
Data retention current	I_{CCDR}	—	1	50*1	µA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	
Operation recovery time	t_R	5	—	—	ms	

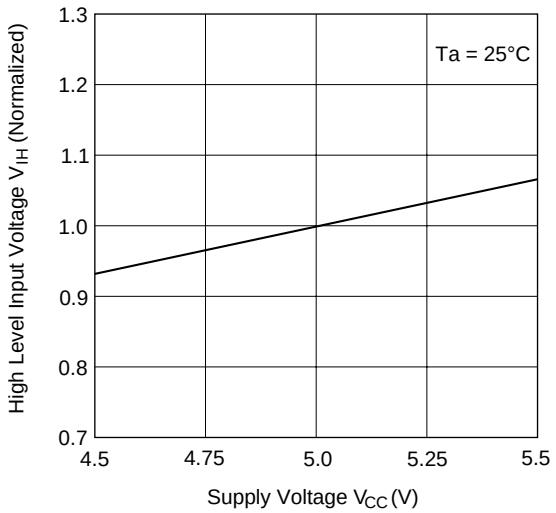
Note: 1. V_{CC} = 3.0 V

Low V_{CC} Data Retention Timing Waveform

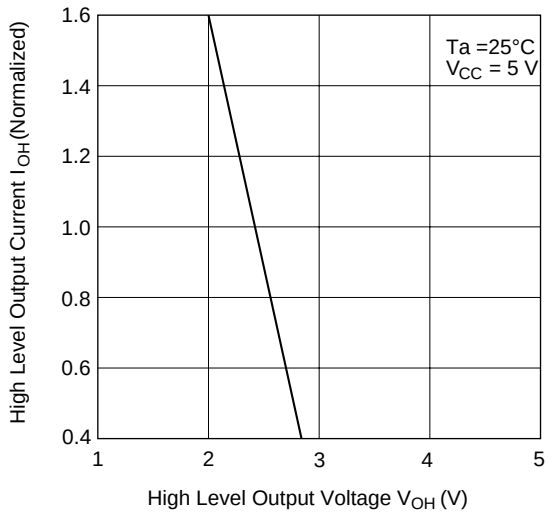




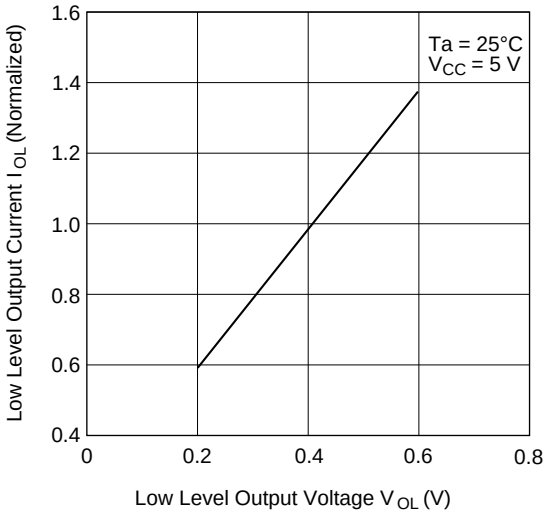
Low Level Input Voltage vs. Supply Voltage



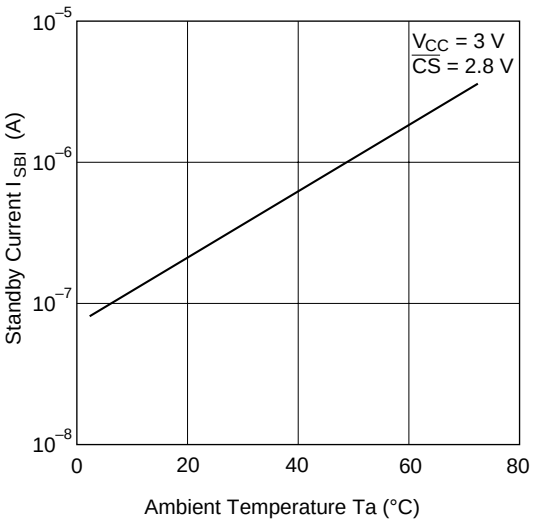
High Level Input Voltage vs. Supply Voltage



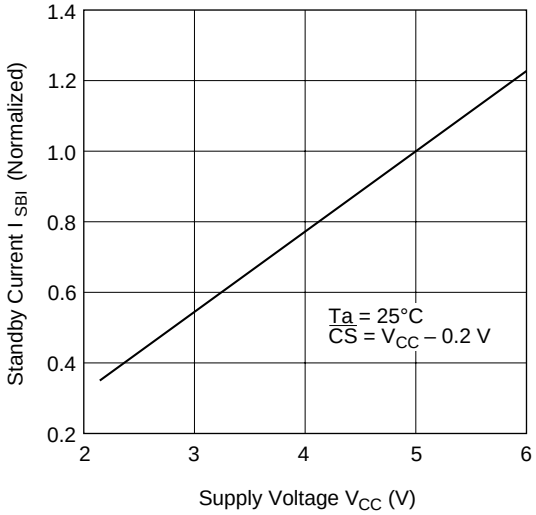
High Level Output Current vs. High Level Output Voltage



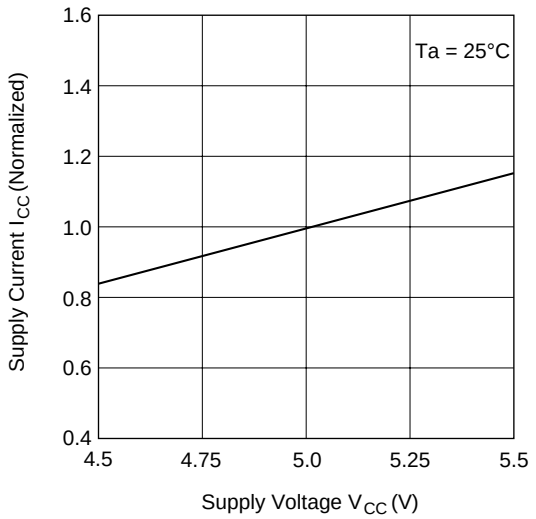
Low Level Output Current vs. Low Level Output Voltage



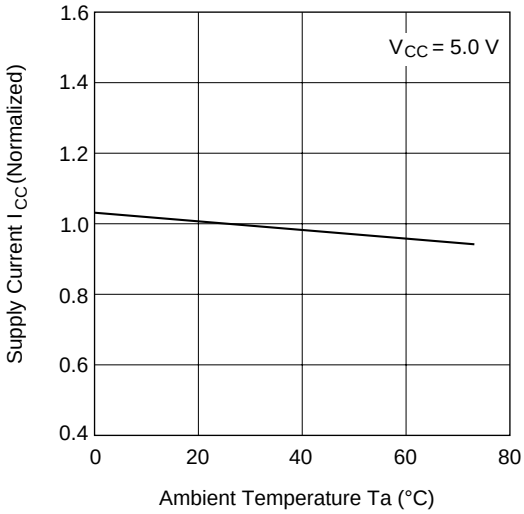
Standby Current vs. Ambient Temperature



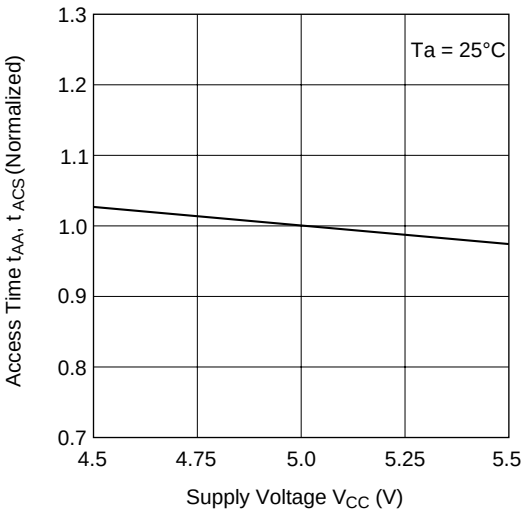
Standby Current vs. Supply Voltage



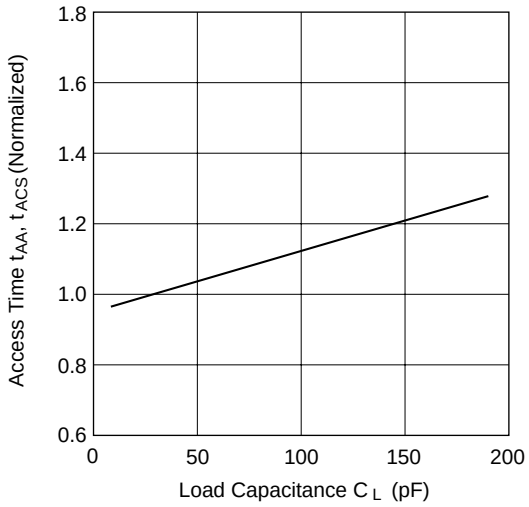
Supply Current vs. Supply Voltage



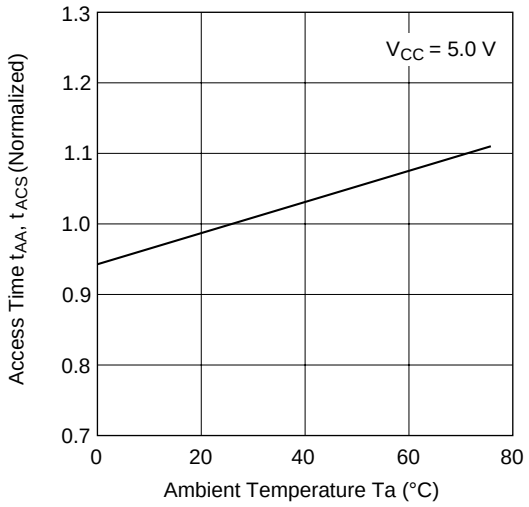
Supply Current vs. Ambient Temperature



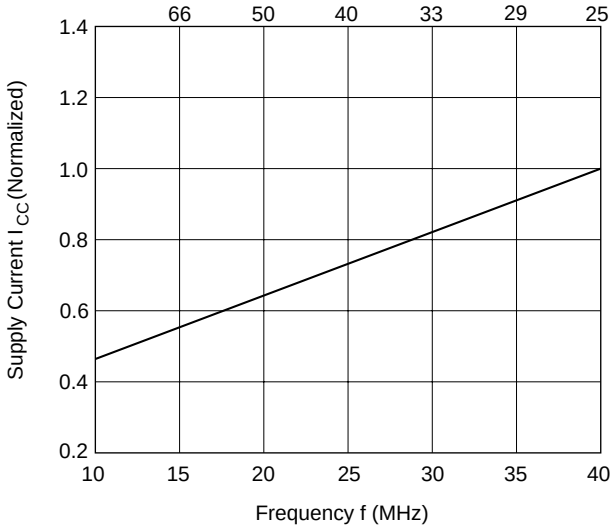
Access Time vs. Supply Voltage



Access Time vs. Load Capacitance



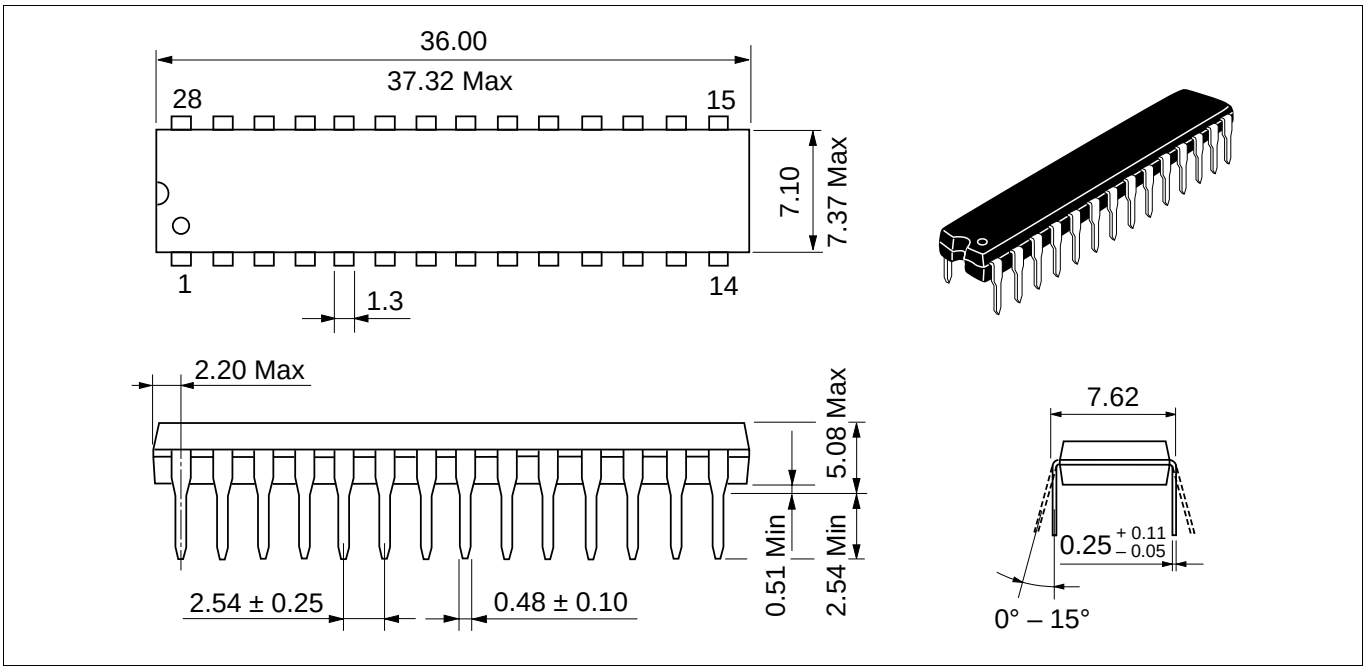
Access Time vs. Ambient Temperature



Supply Current vs. Frequency

Package Dimensions

HM62832HP/HLP Series (DP-28NA) Unit: mm



HM62832HJP/HLJP Series (CP-28DN) Unit: mm